

Title (en)

FIELD EFFECT TRANSISTOR WITH ENHANCED INSULATOR STRUCTURE

Title (de)

FELDEFFEKTTRANSISTOR MIT VERBESSERTER ISOLATORSTRUKTUR

Title (fr)

TRANSISTOR A EFFET DE CHAMP PRESENTANT UNE STRUCTURE ISOLANTE AMELIOREE

Publication

EP 1690286 A4 20090708 (EN)

Application

EP 04817951 A 20041206

Priority

- US 2004040599 W 20041206
- US 52763103 P 20031205

IPC 8 full level

H01L 21/3205 (2006.01); **H01L 21/336** (2006.01); **H01L 21/4763** (2006.01); **H01L 29/20** (2006.01); **H01L 29/739** (2006.01); **H01L 29/778** (2006.01); **H01L 31/0328** (2006.01); **H01L 31/0336** (2006.01); **H01L 31/072** (2006.01); **H01L 31/109** (2006.01)

CPC (source: EP)

H01L 29/2003 (2013.01); **H01L 29/7787** (2013.01)

Citation (search report)

- [X] US 6429467 B1 20020806 - ANDO YUJI [JP]
- [X] US 2002139995 A1 20021003 - INOUE KAORU [JP], et al
- See references of WO 2005057623A2

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IS IT LI LT LU MC NL PL PT RO SE SI SK TR

DOCDB simple family (publication)

EP 1690286 A2 20060816; EP 1690286 A4 20090708

DOCDB simple family (application)

EP 04817951 A 20041206